APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention

METHOD FOR GROWING A GATE OXIDE LAYER ON A SILICON SURFACE WITH PRELIMINARY N2O ANNEAL

Application Type : regular, utility
Attorney Docket Number : NTCP0014USA

Correspondence address:

Customer Number: 027765

Priority Data:

Doc.No: 093107164; Country -TW; Date: 2004-03-17 us-priority-claimed

Inventor Information:

Inventor 1:

Applicant Authority Type: Inventor **Citizenship:** TW

Given Name: Shian-Jyh

Family Name: Lin

Residence:

City of Residence: Chia-Yi Hsien

Country of Residence: TW

Address-1 of Mailing Address: No. 18, Community 1, Ta-Ping-Ting, Yi-Lung Tsun,

Address-2 of Mailing Address: Chu-Chi Hsiang
City of Mailing Address: Chia-Yi Hsien

State of Mailing Address:

Postal Code of Mailing Address:

Country of Mailing Address: TW

Phone: Fax: E-mail:

Attorney Information:

practitioner(s) at Customer Number:

027765



as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.